



# Fabrication of Nanoscale Columnar Diodes by Glancing Angle Deposition

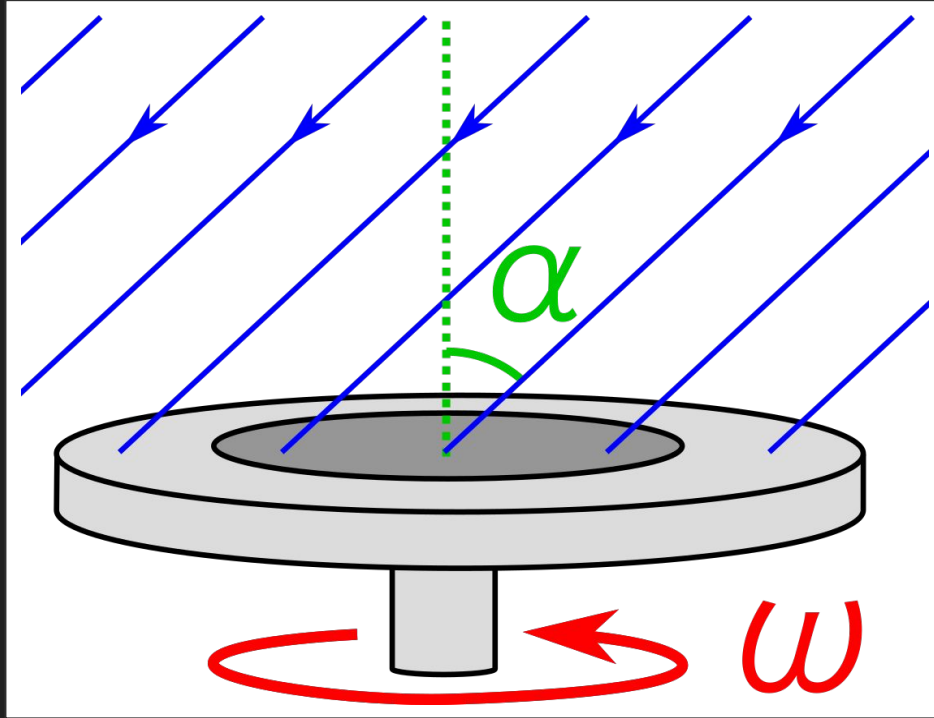
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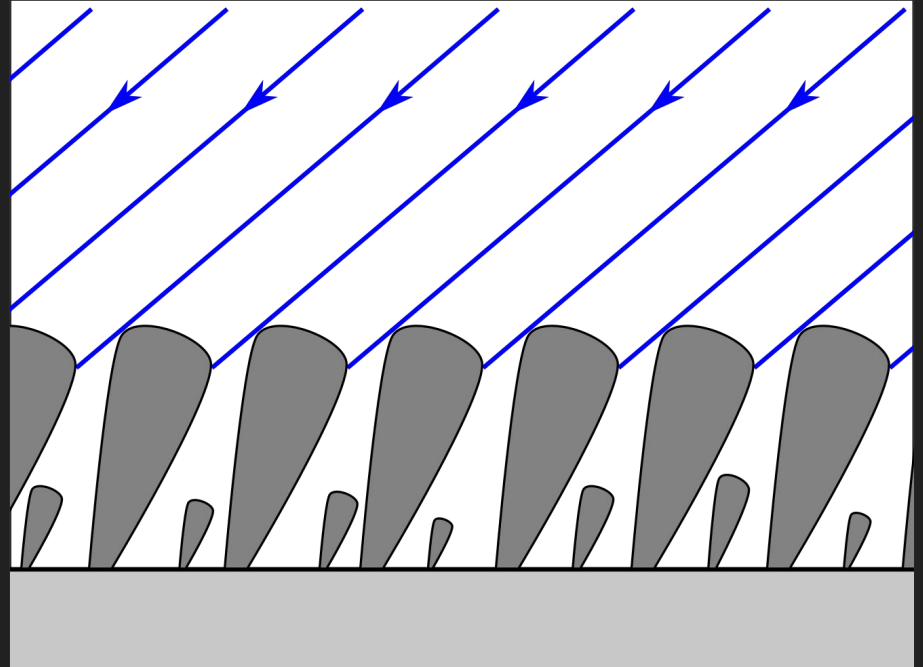
# What is Glancing Angle Deposition (GLAD)?



- Vapor mean free path  $>$  target-substrate separation
- Vapor obliquely incident on substrate
- Substrate rotation precisely controlled

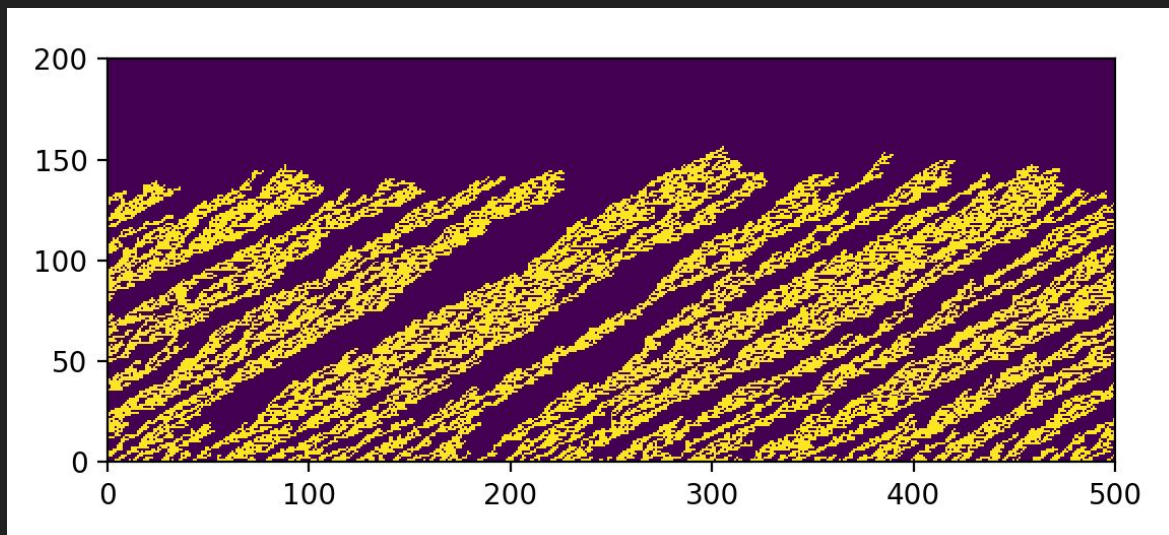
# Why would we do that?

- Vapor follows “line of sight”
- Surface features “cast shadows”
- “Shadowed” areas stop growing
- Competitive growth!

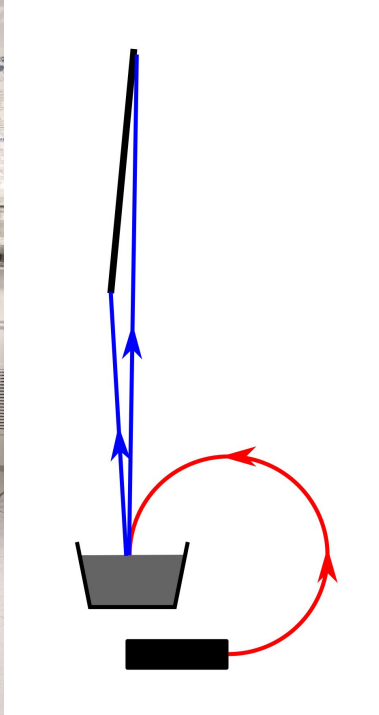
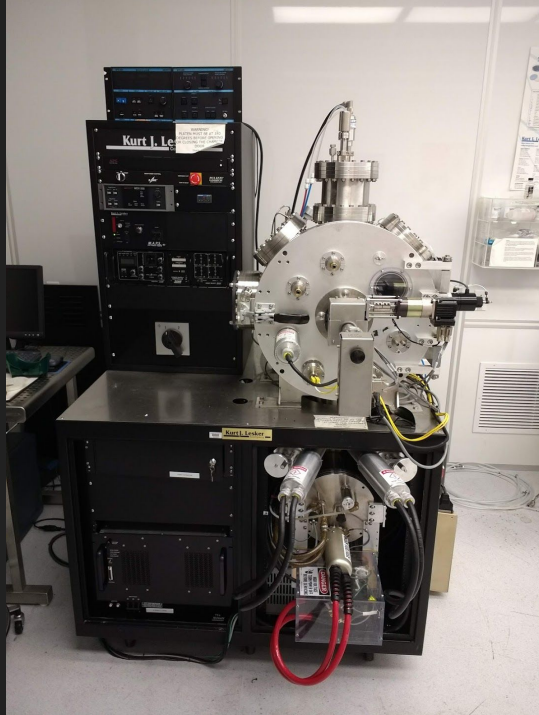


# A simple model of GLAD

- Vapor incident at angle  $\alpha$
- Where it hits, it sticks
- Periodic boundary conditions
- Tilted columns!



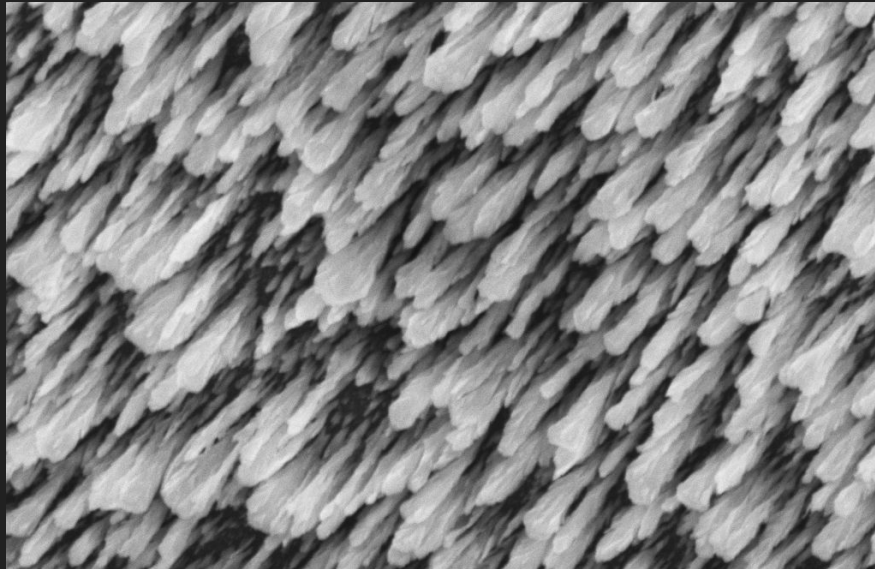
# Let's get GLAD



- We use ebeam
- $\text{MFP} > \text{target substrate separation}$
- Controllable  $\alpha$  and  $\omega$

# Some real GLAD films

$\alpha = 84^\circ$ ,  $\omega = 0$  RPM, dep time = 30 minutes, rotations = 0 rev



100 nm

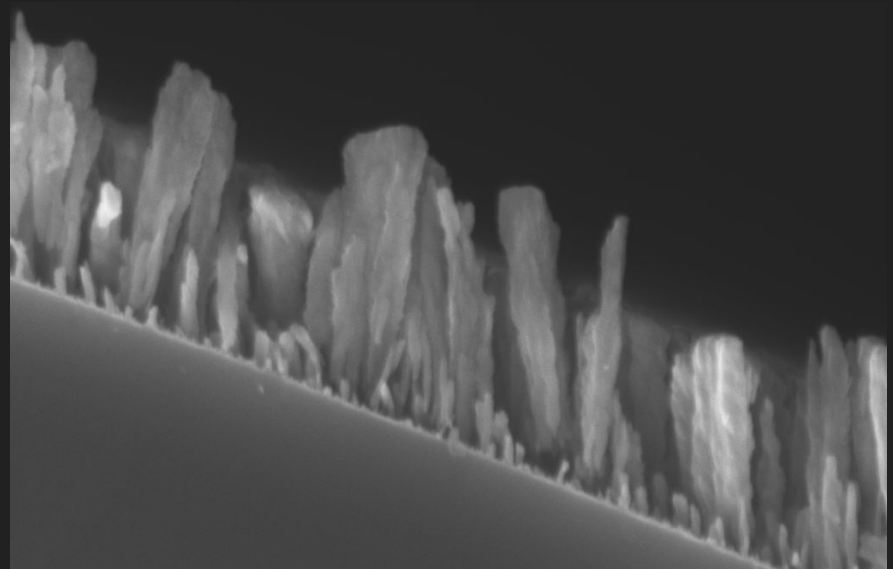
EHT = 5.00 kV  
WD = 6.1 mm

Signal A = InLens



Mag = 29.49 K X Width = 3.877  $\mu$ m  
Reference Mag = Polaroid 545

Date : 26 Jun 2018



100 nm

EHT = 5.00 kV  
WD = 3.9 mm

Signal A = InLens

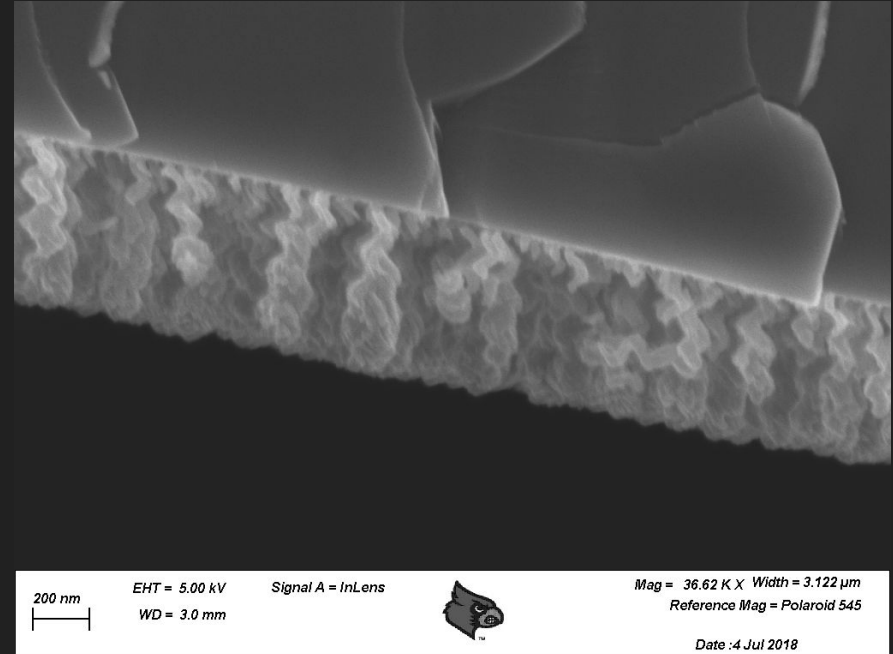
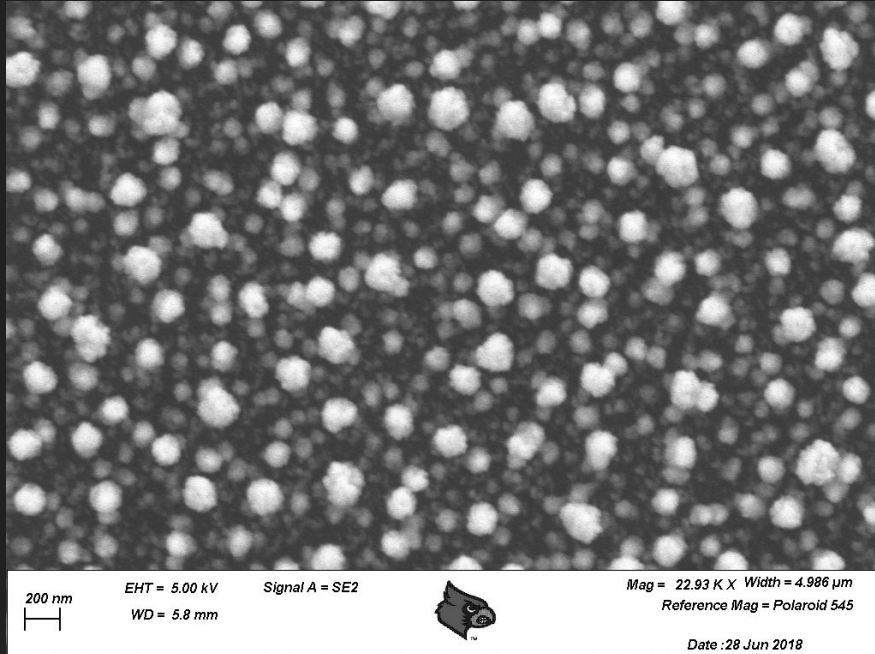


Mag = 49.00 K X Width = 2.333  $\mu$ m  
Reference Mag = Polaroid 545

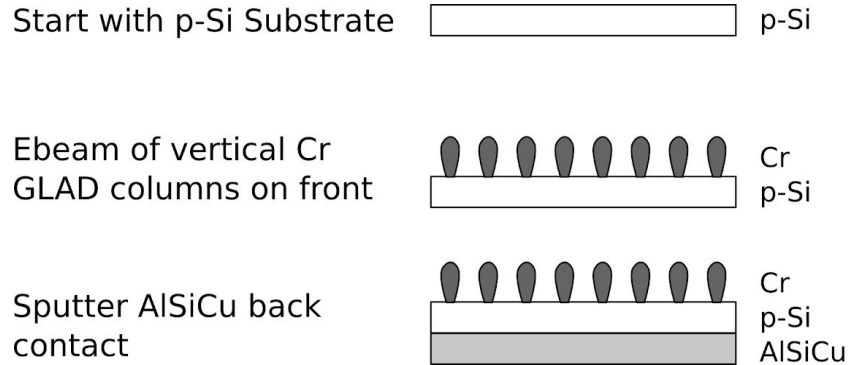
Date : 4 Jul 2018

# Some (more) real GLAD films

$\alpha = 84^\circ$ ,  $\omega = 0.1$  RPM, dep time = 40 minutes, rotations = 4 rev



# What's the simplest device we could possibly make?



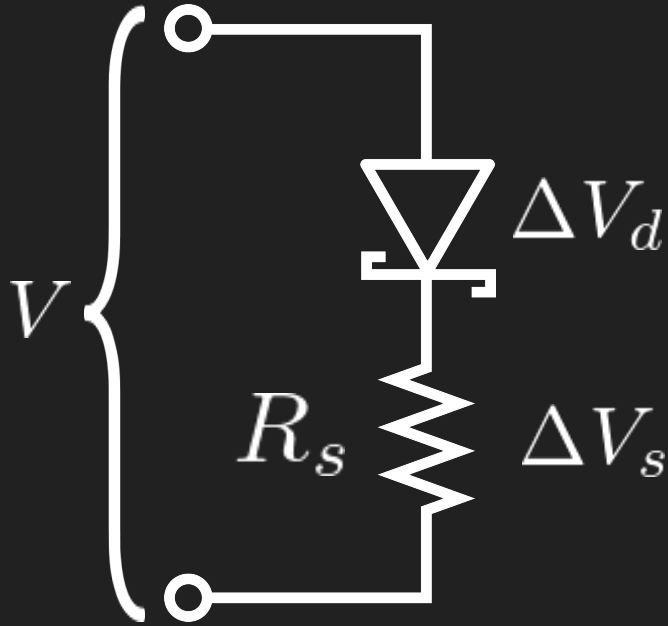
- Schottky Diodes!
  - Metal/Semiconductor junction

$$I = I_s \left( e^{\frac{V}{\eta V_T}} - 1 \right)$$

- Just add a back contact!



## Modeling the device:

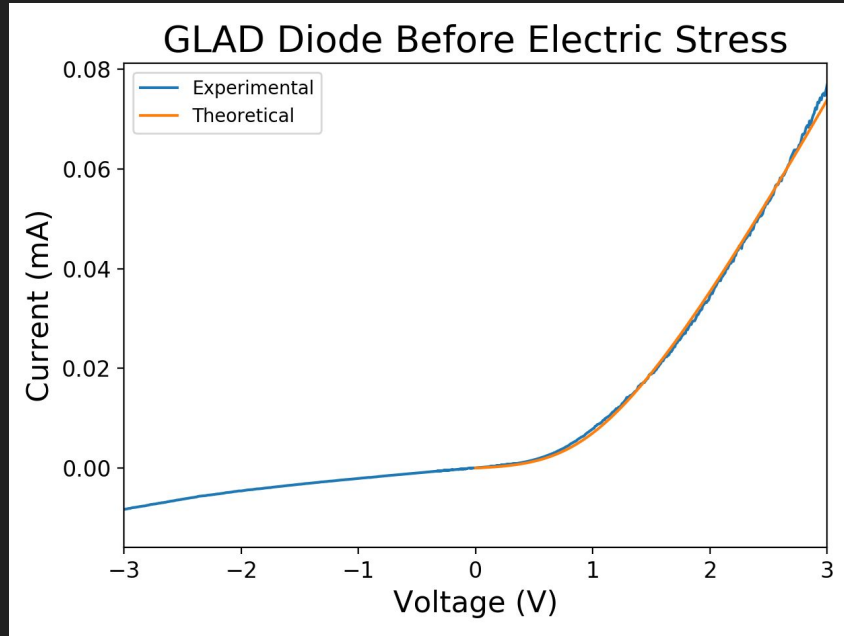


Model diode in forward bias using Shockley diode equation with ideality factor:

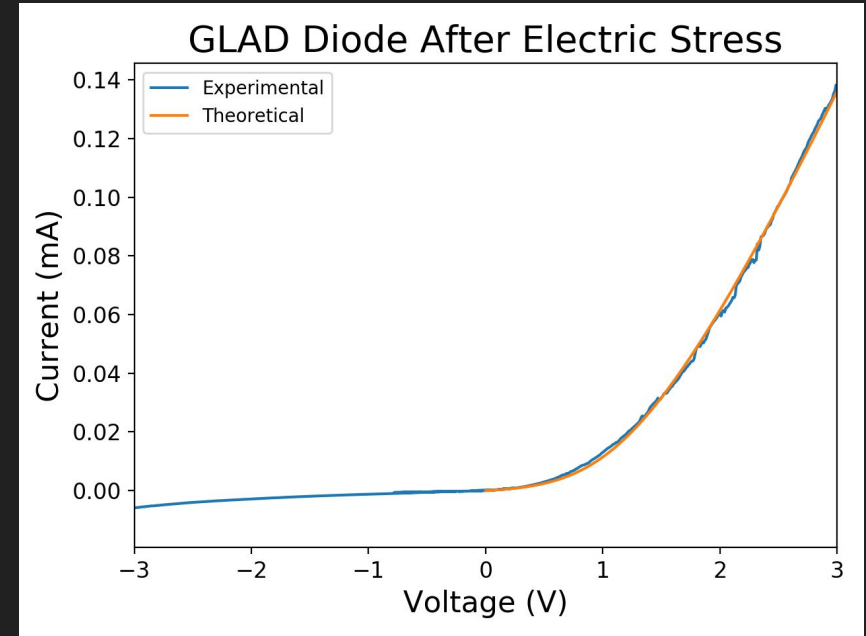
$$I = I_s \left( e^{\frac{\Delta V_d}{\eta V_T}} - 1 \right)$$

$I(V)$  can only be expressed implicitly, so we solve it numerically.

# I-V Characteristics and Curve Fits (GLAD diode)



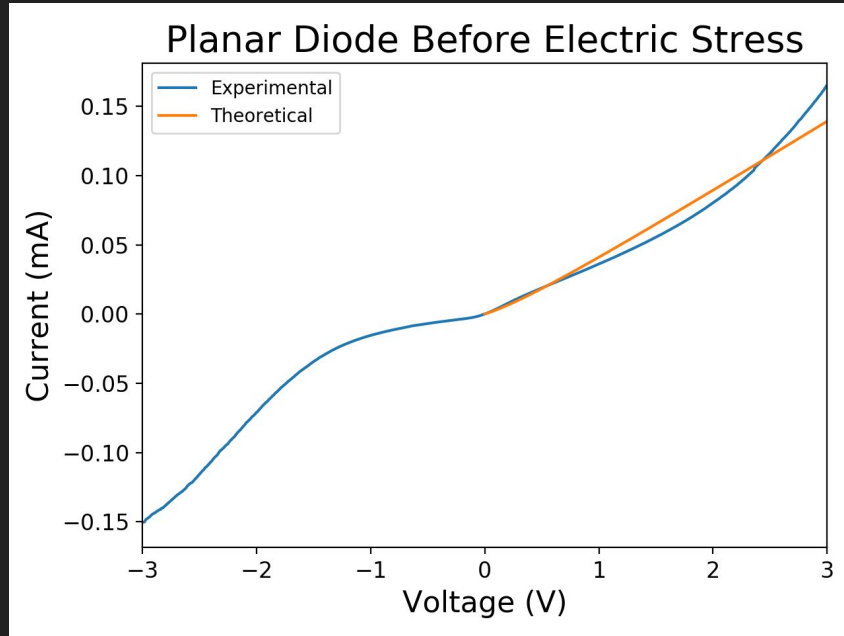
$$I_s = 2.4 \times 10^{-7} \text{ A}, \eta = 9.65, R_s = 21200 \, \Omega$$



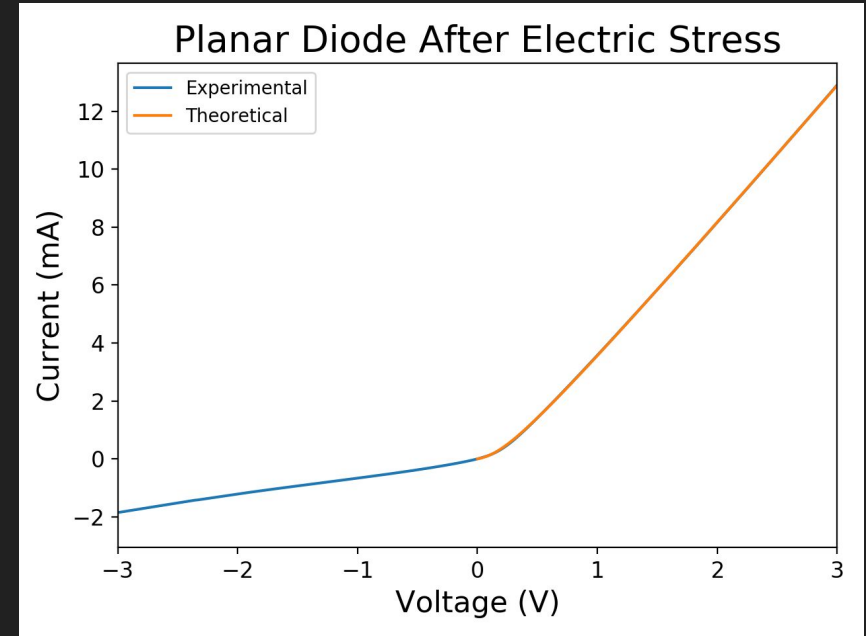
$$I_s = 1.8 \times 10^{-7} \text{ A}, \eta = 8.6, R_s = 11300 \, \Omega$$

Electrical stress: -75V to 75V at 60 Hz

# I-V Characteristics and Curve Fits (planar diode)



$$I_s = 5.0 \times 10^{-7} \text{ A}, \eta = 3.6, R_s = 19300 \Omega$$



$$I_s = 6.1 \times 10^{-6} \text{ A}, \eta = 2.53, R_s = 206 \Omega$$

Electrical stress: -75V to 75V at 60 Hz

# Conclusions

- We successfully made GLAD diodes!
- Ideality factors were higher (bad)
- Series resistances were higher (bad)
- Difficult to interpret difference in currents
- Electrical stress had smaller effect on GLAD diodes
- GLAD diodes better fit the model before electrical stress

